

Lecture 18: Bipolar Junction Transistors (BJTs) III

- Announcements:
- HW#6 online and due Friday Oct. 12 via Gradescope
- PreLab#4 is online and due next week, as is Lab#3
- Lab#4 (the experimental part) will be online soon
- By popular demand, lab sections run this week
- Midterm 1: Friday, Oct. 5, from 5-6:30 p.m., in 277 Cory
- Midterm Info Sheet online with updates from what we discussed last week

 • Lecture Topics:

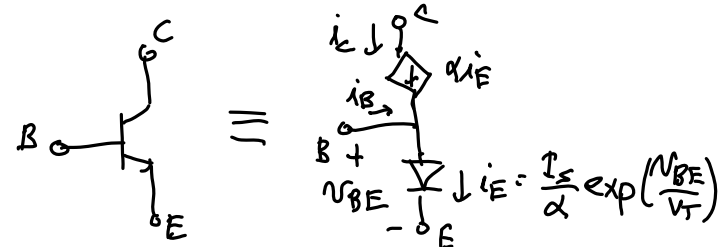
- ↳ BJT Forward-Active Region
 - Physics
 - Large Signal Circuit Model
 - Operating Pt. Example
- ↳ Reverse Active Region
- ↳ Saturation Region

 • Last Time:

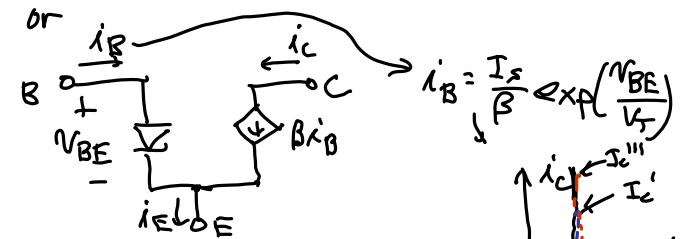
- Forward-active BJT large signal model
- Now, continue with this

Equiv. Large Signal Ckt. Models for BJTs (in Forward-Active)

⇒ several of them → two most popular accurate ones:

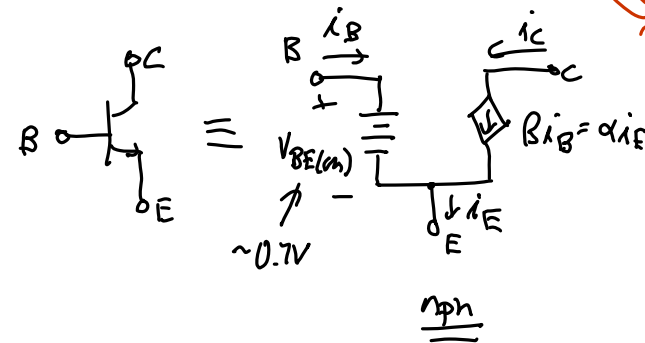


Common-Base (CCB)



Common-Emitter (CE)

↳ usually, won't use the above, but rather will use:
 ~0.7V



(for pnp)

$B i_B = \alpha i_E$

Example. (exactitude)

Find the DC operating pt.
 (i.e., find the DC voltages at each node and the currents through each branch)

$V_{CC} = +15$
 $R_C = 5k\Omega$
 $V_{BE} = 0.7V$
 $R_E = 7k\Omega$
 $V_{EE} = -15V$

$I_E = \frac{-V_{BE} - V_{EE}}{R_E}$

$I_C = \alpha I_E = \frac{\alpha(-V_{EE} - V_{BE})}{R_E}$

For npn β istor:
 $\beta = 100$
 $I_S = 2 \times 10^{-15} A$

$I_S \exp\left(\frac{V_{BE}}{V_T}\right) = \frac{\beta}{\beta + 1} \frac{(-V_{EE} - V_{BE})}{R_E}$
 25mV (nonlinear equation)

iteration, numerical \rightarrow painful...

\Rightarrow Get $V_{BE} = 0.717V$ $V_B = 0V$
 $\Rightarrow I_E = \frac{15 - 0.717}{7k} = 2.04mA$ $V_E = -0.717V$
 $\Rightarrow I_C = \alpha I_E = \left(\frac{100}{101}\right) I_E = 2.02mA$ $V_C = 15 - I_C(5k) = 4.9V$
 $\Rightarrow I_B = \frac{I_C}{\beta} = 0.02mA$

\Rightarrow What if we don't know β or I_S accurately? \rightarrow No need to be so accurate!

\Rightarrow Do the problem again using approximations. \rightarrow esp. the model.

$V_B = 0V, V_E = -0.7V = -V_{BE(m)}$

$I_E = \frac{-0.7 - (-15)}{7k} \approx 2.04mA$

$I_C = \alpha I_E \approx I_E = 2.04mA$

$I_B = \frac{I_C}{\beta} = 0.02mA$

$V_C = 15 - (2.04m)(5k) = 4.8V$
 $10^{-3} \quad 10^3$

\Rightarrow no exponential
 \Rightarrow easy to solve!

③ Reverse-Active Region:

BEJ reverse-biased
BCJ forward-biased

⇒ similar to forward-active region w/ one important difference:

$$\beta_R \propto \frac{N_{dc}W_cD_p}{N_{db}W_bD_n} \leftarrow N_{dc} < N_{db} \text{ (collector is } n\text{-)}$$

∴ $\beta_R \ll \beta_F$

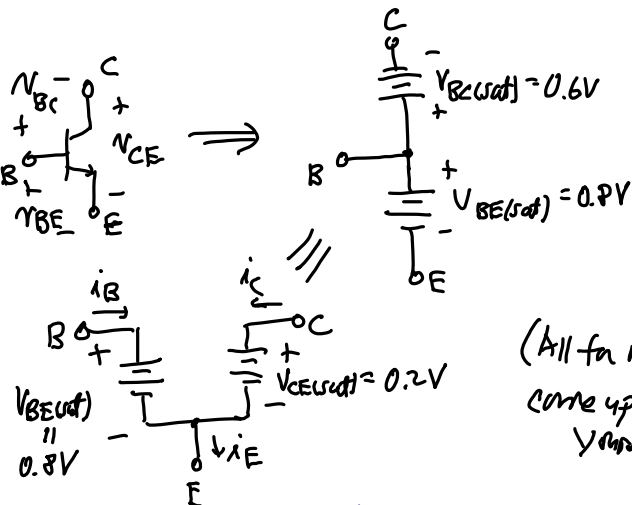
↑ reverse ∴ $\beta_F \ll \beta_R$ forward

Thus, avoid using the device in reverse-active!

higher than 0.7V in saturation

④ Saturation Region:

BEJ forward-biased → $V_{BE(on)} \sim 0.8V$
BCJ forward-biased → $V_{BE(on)} \sim 0.6V$

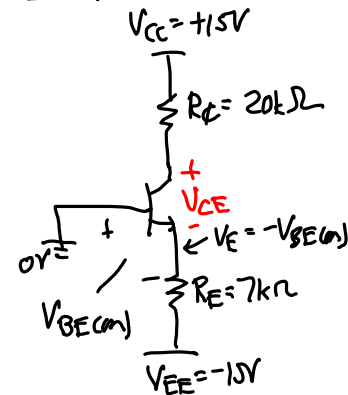


(All for npn; come up w/ prop. values)

• When determining DC operating point:

1. First, assume forward-active, then check for cut-off, i.e., is there enough V_{BE} ?
2. Assume forward-active, then determine V_{CE} .
3. If $V_{CE} > V_{CE(sat)}$, then okay ... otherwise, must do analysis using the device saturation model.

Example.

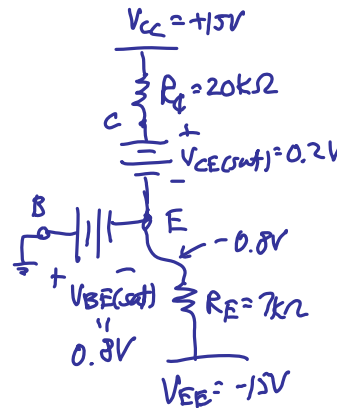


① $i_E = \frac{15 - 0.7}{7k} = 2.04mA$
⇒ enough voltage to turn on BJT ✓

② Assume forward-active

$V_C = 15 - (2.04mA)(20k) = -25.8V$
∴ $V_{CE} = V_C - V_E = -25.8 - (-0.7) = -25.1V < \underbrace{-0.2V}_{V_{CE(sat)}}$
∴ saturated BJT

③ Analyze assuming saturation:



$V_B = 0V, V_E = -0.8V$
 $I_E = \frac{-0.8 + 15}{7k} = 2.03mA$
 $I_C = \frac{15 - (-0.8) - 0.2}{20k} = \underline{0.78mA}$
 $I_B = I_E - I_C = 1.25mA$
(Note: no longer $I_B = \frac{I_C}{\beta}$)
 $V_C = 15 - (0.78mA)(20k) = -0.6V$